



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)} max	I _D max T _A = +25°C		
2017	16mΩ @ V _{GS} = 10V	9.8A		
30V	22mΩ @ V _{GS} = 4.5V	8.4A		

Description

This MOSFET has been designed to minimize the on-state resistance (R_{DS(on)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Backlighting
- **Power Management Functions**
- DC-DC Converters

Features and Benefits

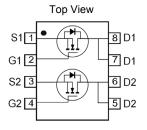
- 100% avalanche rated part
- Low R_{DS(on)} minimizes conduction losses
- Low Q_q minimizes switching losses
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

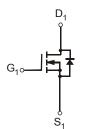
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.076 grams (approximate)



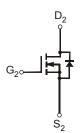
Top View



Pin Configuration Internal Schematic



N-Channel MOSFET



N-Channel MOSFET

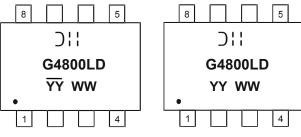
Ordering Information (Notes 4 & 5)

Part Number	Compliance	Case	Packaging
DMG4800LSD-13	Standard	SO-8	2,500 / Tape & Reel
DMG4800LSDQ-13	Automotive	SO-8	2,500 / Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q10x and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



Shanghai A/T Site

⊃¦¦ = Manufacturer's Marking G4800LD = Product Type Marking Code YYWW = Date Code Marking YY or \overline{YY} = Year (ex: 14 = $2\overline{0}$ 14) WW = Week (01 - 53)

YY = Date Code Marking for SAT (Shanghai Assembly/ Test site) YY = Date Code Marking for CAT (Chengdu Assembly/ Test site)

Chengdu A/T Site



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage	_		V_{GSS}	±25	V
Continuous Prain Current (Note 7) / - 40 /	Steady State	T _A = +25°C T _A = +70°C	I _D	7.5 6.0	А
Continuous Drain Current (Note 7) V _{GS} = 10V	t<10s	T _A = +25°C T _A = +70°C	I _D	9.8 7.7	Α
Continuous Drain Compart (Note 7) / - 4 5/	Steady State	T _A = +25°C T _A = +70°C	I _D	6.4 5.0	Α
Continuous Drain Current (Note 7) V _{GS} = 4.5V	t<10s	T _A = +25°C T _A = +70°C	I _D	8.4 6.6	Α
Maximum Continuous Body Diode Forward Current (Note 7)			Is	2	Α
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I _{DM}	42	Α
Avalanche Current (Notes 8 & 9) L = 0.1mH			I _{AR}	17	Α
Repetitive Avalanche Energy (Notes 8 & 9) L = 0.1mH			E _{AR}	14	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Units	
Total Power Dissipation (Note 6)		P_{D}	1.17	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{0JA}	107	°C/W	
Thermal Resistance, Junction to Ambient (Note 6)	t<10s		61]	
Total Power Dissipation (Note 7)		P_{D}	1.5	W	
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	Ъ	83	°C/W	
Thermal Resistance, Junction to Ambient (Note 1)	t<10s	$R_{\theta JA}$	49		
Thermal Resistance, Junction to Case		$R_{ heta JC}$	14.5		
Operating and Storage Temperature Range		$T_{J_1}T_{STG}$	-55 to 150	°C	

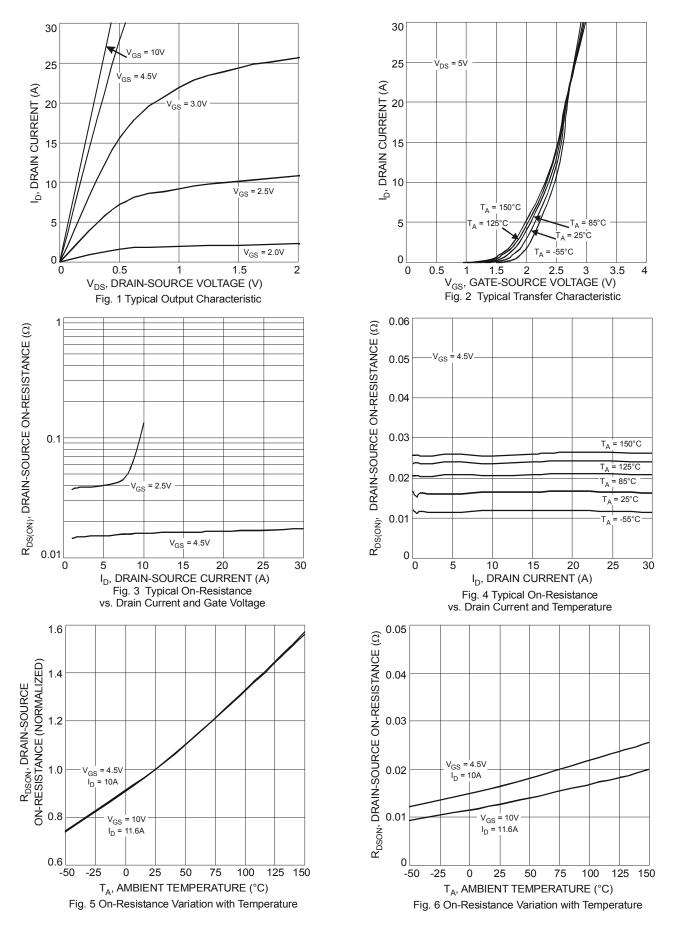
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 10)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	-	_	1.0	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 10)							
Gate Threshold Voltage	$V_{GS(th)}$	8.0		1.6	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	D		12	16 22	mΩ	$V_{GS} = 10V, I_D = 9A$	
Static Dialii-Source Off-Resistance	R _{DS(on)}		16			$V_{GS} = 4.5V, I_D = 7A$	
Forward Transfer Admittance	Y _{fs}	1	8	_	S	$V_{DS} = 10V, I_{D} = 9A$	
Diode Forward Voltage	V_{SD}	_	0.72	0.94	V	$V_{GS} = 0V$, $I_S = 1A$	
DYNAMIC CHARACTERISTICS (Note 11)							
Input Capacitance	C _{iss}	-	798	_	pF	101/11/	
Output Capacitance	Coss	1	128		pF	$V_{DS} = 10V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	C_{rss}	_	122		pF	1 - 1.0WH12	
Gate Resistance	R_g	_	1.37	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg	_	8.56		nC	\\\ 5\\\\\ 45\\	
Gate-Source Charge	Q_{gs}	_	1.8	_	nC	$V_{GS} = 5V, V_{DS} = 15V,$ $I_{D} = 9A$	
Gate-Drain Charge	Q_{gd}	_	2.5	_	nC		
Turn-On Delay Time	$t_{D(on)}$	_	5.03	_	ns		
Turn-On Rise Time	t _r	_	4.50	_	ns	V _{DD} = 15V, V _{GEN} = 10V,	
Turn-Off Delay Time	t _{D(off)}	_	26.33	_	ns	$R_L = 15\Omega$, $R_G = 6\Omega$, $I_D = 1A$	
Turn-Off Fall Time	t _f	_	8.55	_	ns		

Notes:

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 8. I_{AR} and E_{AR} rating are based on low frequency and duty cycles to keep T_J = +25°C.
 9. Applicable to products manufactured with Data Code "1146" (Nov, 2011) and newer.
 10. Short duration pulse test used to minimize self-heating effect.
 11. Guaranteed by design. Not subject to product testing.







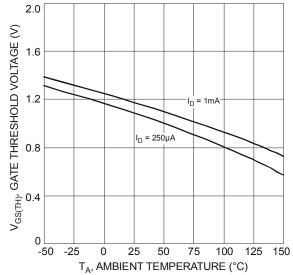
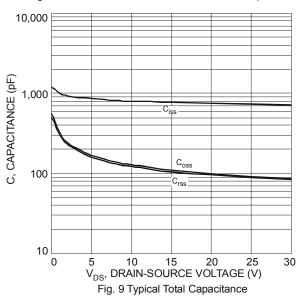


Fig. 7 Gate Threshold Variation vs. Ambient Temperature



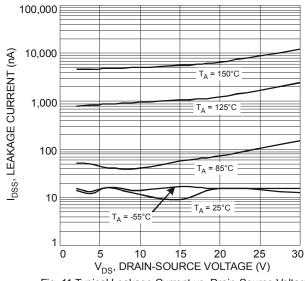
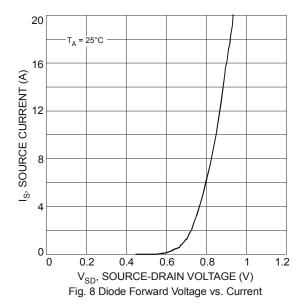
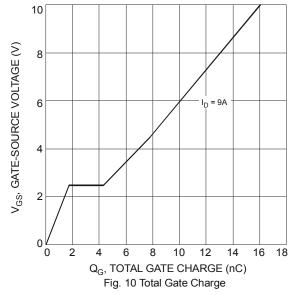
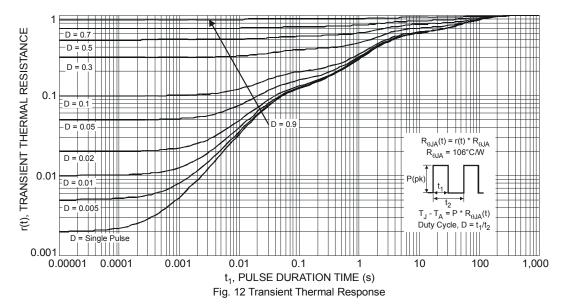


Fig. 11 Typical Leakage Current vs. Drain-Source Voltage



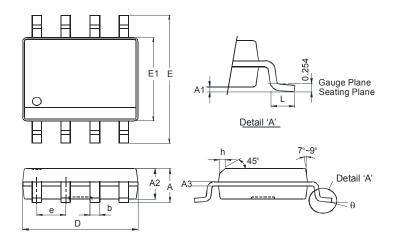






Package Outline Dimensions

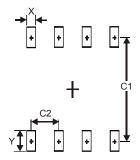
Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



SO-8						
Dim	Min	Max				
Α	-	1.75				
A1	0.10	0.20				
A2	1.30	1.50				
Α3	0.15	0.25				
b	0.3	0.5				
D	4.85	4.95				
Е	5.90	6.10				
E1	3.85	3.95				
е	e 1.27 Typ					
h	-	0.35				
L	0.62	0.82				
θ	0°	8°				
All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)				
X	0.60				
Υ	1.55				
C1	5.4				
C2	1.27				



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